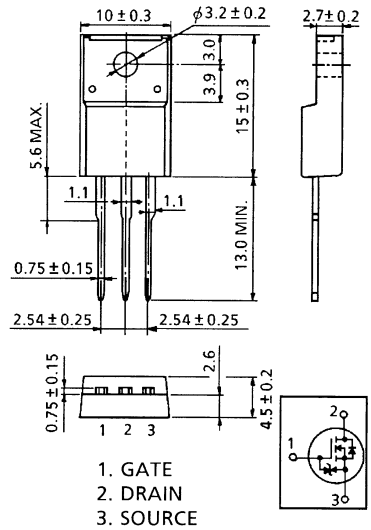
# 2SK4111

Switching Regulator Applications

- Low drain-source ON resistance: $R_{DS\ (ON)}$ = 0.54 Ω (typ.)
- High forward transfer admittance: $|Y_{fs}|$ = 8.5 S (typ.)
- Low leakage current: $I_{DSS}$ = 100 μA (max) ($V_{DS}$ = 600 V)
- Enhancement mode: $V_{th}$ = 2.0 to 4.0 V ($V_{DS}$ = 10 V, $I_D$ = 1 mA)

Unit: mm




| | |
|---|---|
| JEDEC | — |
| JEITA | SC-67 |
| TOSHIBA | 2-10R1B |

Weight: 1.9 g (typ.)

## Absolute Maximum Ratings (Ta = 25°C)

| Characteristics | | Symbol | Rating | Unit |
|---|---|---|---|---|
| Drain-source voltage | | $V_{DSS}$ | 600 | V |
| Drain-gate voltage ($R_{GS}$ = 20 kΩ) | | $V_{DGR}$ | 600 | V |
| Gate-source voltage | | $V_{GSS}$ | ±30 | V |
| Drain current | DC (Note 1) | $I_D$ | 10 | A |
| | Pulse (t = 1 ms) (Note 1) | $I_{DP}$ | 40 | |
| Drain power dissipation (Tc = 25°C) | | $P_D$ | 45 | W |
| Single pulse avalanche energy (Note 2) | | $E_{AS}$ | 363 | mJ |
| Avalanche current | | $I_{AR}$ | 10 | A |
| Repetitive avalanche energy (Note 3) | | $E_{AR}$ | 4.5 | mJ |
| Channel temperature | | $T_{ch}$ | 150 | °C |
| Storage temperature range | | $T_{stg}$ | -55 to 150 | °C |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook (“Handling Precautions”/“Derating Concept and Methods“) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

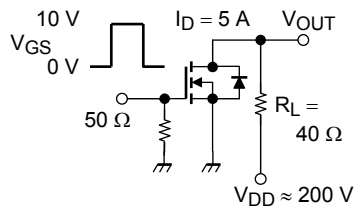
## Thermal Characteristics

| Characteristics | Symbol | Max | Unit |
|---|---|---|---|
| Thermal resistance, channel to case | $R_{th\ (ch-c)}$ | 2.78 | °C/W |
| Thermal resistance, channel to ambient | $R_{th\ (ch-a)}$ | 62.5 | °C/W |

Note 1: Ensure that the channel temperature does not exceed 150℃.

Note 2: $V_{DD}$ = 90 V, $T_{ch}$ = 25°C(initial), L = 6.36 mH, $I_{AR}$ = 10 A, $R_G$ = 25 Ω

## Electrical Characteristics (Ta = 25°C)

| Characteristics | | Symbol | Test Condition | Min | Typ. | Max | Unit |
|---|---|---|---|---|---|---|---|
| Gate leakage current | | $I_{GSS}$ | $V_{GS}$ = ±25 V, $V_{DS}$ = 0 V | — | — | ±10 | μA |
| Gate-source breakdown voltage | | $V_{(BR)\ GSS}$ | $I_G$ = ±10 μA, $V_{DS}$ = 0 V | ±30 | — | — | V |
| Drain cut-off current | | $I_{DSS}$ | $V_{DS}$ = 600 V, $V_{GS}$ = 0 V | — | — | 100 | μA |
| Drain-source breakdown voltage | | $V_{(BR)\ DSS}$ | $I_D$ = 10 mA, $V_{GS}$ = 0 V | 600 | — | — | V |
| Gate threshold voltage | | $V_{th}$ | $V_{DS}$ = 10 V, $I_D$ = 1 mA | 2.0 | — | 4.0 | V |
| Drain-source ON resistance | | $R_{DS\ (ON)}$ | $V_{GS}$ = 10 V, $I_D$ = 5 A | — | 0.54 | 0.75 | Ω |
| Forward transfer admittance | | $\|Y_{fs}\|$ | $V_{DS}$ = 10 V, $I_D$ = 5 A | 2.4 | 8.5 | — | S |
| Input capacitance | | $C_{iss}$ | $V_{DS}$ = 25 V, $V_{GS}$ = 0 V, f = 1 MHz | — | 1500 | — | pF |
| Reverse transfer capacitance | | $C_{rss}$ | | — | 15 | — | |
| Output capacitance | | $C_{oss}$ | | — | 180 | — | |
| Switching time | Rise time | $t_r$ |  | — | 22 | — | ns |
| | Turn-on time | $t_{on}$ | | — | 50 | — | |
| | Fall time | $t_f$ | | — | 36 | — | |
| | Turn-off time | $t_{off}$ | Duty ≤ 1%, $t_w$ = 10 μs | — | 180 | — | |
| Total gate charge | | $Q_g$ | $V_{DD}$ ≈ 400 V, $V_{GS}$ = 10 V, $I_D$ = 10 A | — | 42 | — | nC |
| Gate-source charge | | $Q_{gs}$ | | — | 23 | — | |
| Gate-drain charge | | $Q_{gd}$ | | — | 19 | — | |



## Source-Drain Ratings and Characteristics (Ta = 25°C)

| Characteristics | Symbol | Test Condition | Min | Typ. | Max | Unit |
|---|---|---|---|---|---|---|
| Continuous drain reverse current (Note 1) | $I_{DR}$ | — | — | — | 10 | A |
| Pulse drain reverse current (Note 1) | $I_{DRP}$ | — | — | — | 40 | A |
| Forward voltage (diode) | $V_{DSF}$ | $I_{DR}$ = 10 A, $V_{GS}$ = 0 V | — | — | −1.7 | V |
| Reverse recovery time | $t_{rr}$ | $I_{DR}$ = 10 A, $V_{GS}$ = 0 V, $dI_{DR}/dt$ = 100 A/μs | — | 1300 | — | ns |
| Reverse recovery charge | $Q_{rr}$ | | — | 16 | — | μC |

## Marking